Inventor: Robert J. Hillard

"METHOD OF ELECTRICAL CHARACTERIZATION OF A SILICON-ON-INSULATOR (SOI)

WAFER" Attorney Docket No.: 1880-031249 Application No.: 10/701,841 1/6 32 -34 MEASUREMENT MEANS FOR ELECTRICAL APPL YING STIMULUS MEANS SEMICONDUCTOR CHUCK SUBSTRATE ELECTRIC LAYER VACUUM ∞ FORMING CONTACT MEANS

Inventor: Robert J. Hillard
"METHOD OF ELECTRICAL CHARACTERIZATION OF A SILICON-ON-INSULATOR (SOI)
WAFER"

MAY 0 5 2005 E

Attorney Docket No.: 1880-031249 Application No.: 10/701,841



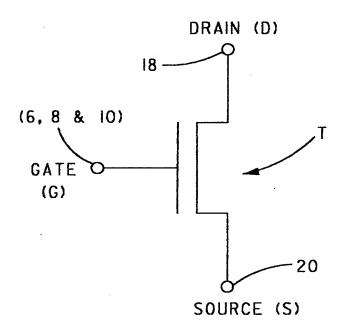


FIG. 2

WAFER"
Attorney Docket No.: 1880-031249 Application No.: 10/701,841

3/6

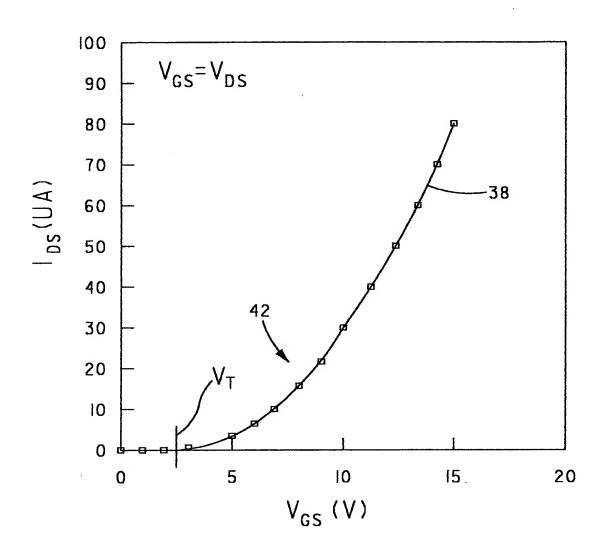


FIG. 3

Attorney Docket No.: 1880-031249 Application No.: 10/701,841

⁴/₆

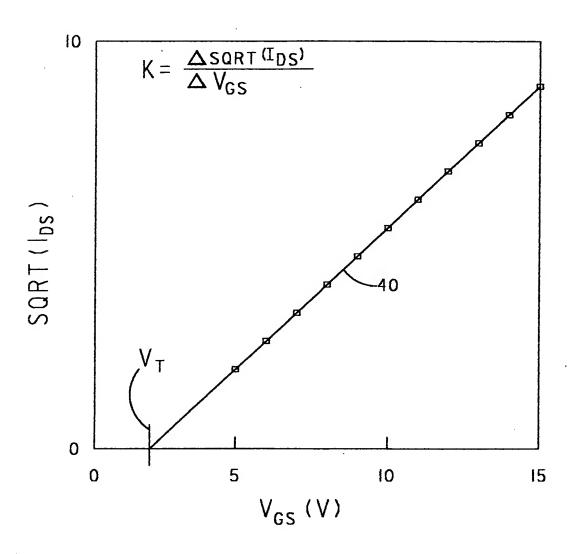


FIG. 4

Attorney Docket No.: 1880-031249 Application No.: 10/701,841



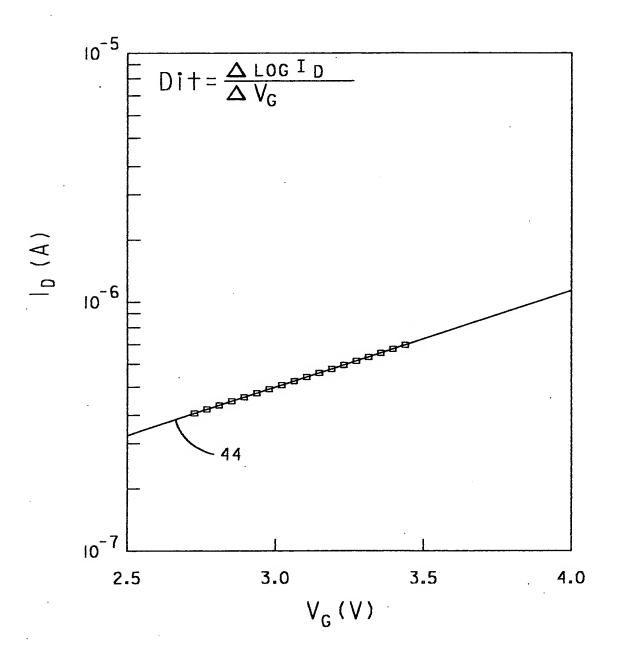


FIG. 5

Inventor: Robert J. Hillard "METHOD OF ELECTRICAL CHARACTERIZATION OF A SILICON-ON-INSULATOR (SOI)
WAFER"
Attorney Docket No.: 1880-031249 Application No.: 10/701,841



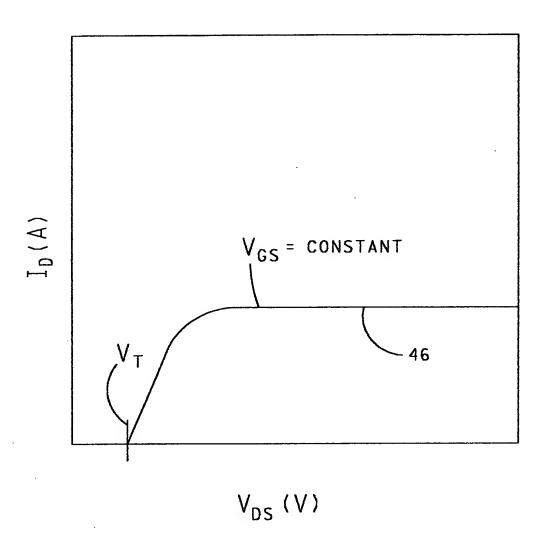


FIG. 6